

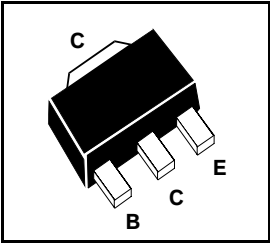
**SOT89 PNP SILICON PLANAR
HIGH VOLTAGE TRANSISTOR**

ISSUE 3 - JANUARY 1996 ⚙

BFN19

COMPLEMENTARY TYPE - BFN18

PARTMARKING DETAIL - DH



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-500	mA
Continuous Collector Current	I_C	-200	mA
Base Current	I_B	-100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	-1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300		V	$I_C = -1mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}		-100 -20	nA μA	$V_{CB} = -250V$ $V_{CB} = -250V, T_{amb} = 150^{\circ}C$
Emitter Cut-Off Current	I_{EBO}		-100	nA	$V_{EB} = -3V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.5	V	$I_C = -20mA, I_B = -2mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	V	$I_C = -20mA, I_B = -2mA$
Static Forward Current Transfer Ratio	h_{FE}	25 40 30			$I_C = -1mA, V_{CE} = -10V^*$ $I_C = -10mA, V_{CE} = -10V^*$ $I_C = -30mA, V_{CE} = -10V^*$
Transition Frequency	f_T	Typ. 100		MHz	$I_C = -20mA, V_{CE} = -10V$ $f = 20MHz$
Output Capacitance	C_{obo}	Typ. 2.5		pF	$V_{CB} = -30V, f = 1MHz$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FMMTA92 datasheet.